

Abstract of the Disclosure

A method of forming a memory device includes preparing a substrate having predefined characteristics; forming a first layer set on the substrate, including: building a first forming layer, having first form segments, on the substrate; building placeholder sidewalls on the first form segments wherein the sidewalls have a thickness of between about one nm and 100 nm; building a second forming layer, having second form segments, on the substrate between the placeholder sidewalls; removing the placeholder sidewalls forming vacated areas; and building active devices in the vacated areas.

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